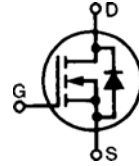


# High Current MegaMOS™ FET

IXTK 110N30

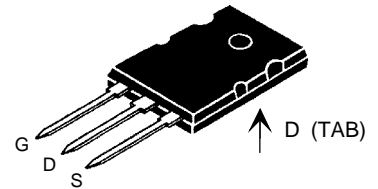
$$\begin{aligned} V_{DSS} &= 300 \text{ V} \\ I_{D25} &= 110 \text{ A} \\ R_{DS(on)} &= 26 \text{ m}\Omega \end{aligned}$$

N-Channel Enhancement Mode



Symbol	Test conditions	Maximum ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	300	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1.0 \text{ M}\Omega$	300	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$ MOSFET chip capability	110	A
$I_{D(RMS)}$	External lead current limit	75	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	440	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	90	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	80	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	4.0	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	730	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.063 in.) from case for 10 s	300	$^\circ\text{C}$
$M_d$	Mounting torque	0.7/6	Nm/lb.in.
<b>Weight</b>	TO-264	10	g

TO-264 AA (IXTK)



G = Gate      D = Drain  
S = Source      Tab = Drain

## Features

- Low  $R_{DS(on)}$  HDMOS™ process
- Rugged polysilicon gate cell structure
- International standard package
- Fast switching times

## Applications

- Motor controls
- DC choppers
- Switched-mode power supplies

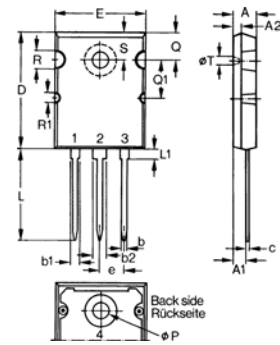
## Advantages

- Easy to mount with one screw (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 1 \text{ mA}$	300		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$	2.0		V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V DC}$ , $V_{DS} = 0$			$\pm 200 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$ , $T_J = 125^\circ\text{C}$			50 $\mu\text{A}$ 3 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \text{ ms}$ , duty cycle $d \leq 2\%$			26 m $\Omega$

Symbol	Test Conditions	Characteristic values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10 V; I_D = 0.5 I_{D25}$ , pulse test	85	101	S
$C_{iss}$	$V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz$		7800	pF
$C_{oss}$			1700	pF
$C_{rss}$			600	pF
$t_{d(on)}$	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1.0 \Omega$ (External)		30	ns
$t_r$			40	ns
$t_{d(off)}$			110	ns
$t_f$			30	ns
$Q_{g(on)}$	$V_{GS} = 10 V, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		390	nC
$Q_{gs}$			60	nC
$Q_{gd}$			180	nC
$R_{thJC}$				0.17 K/W
$R_{thCK}$		0.15		K/W

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.066
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

### Source-Drain Diode

### Ratings and Characteristics

( $T_j = 25^\circ C$  unless otherwise specified)

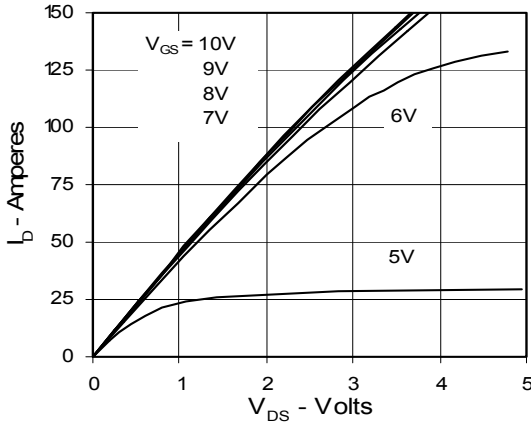
Symbol	Test Conditions	Min.	Typ.	Max.
$I_s$	$V_{GS} = 0V$			110 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			440 A
$V_{SD}$	$I_F = I_s, V_{GS} = 0 V$ , Pulse test, $t \leq 300 \mu s$ , duty cycle $d \leq 2 \%$			1.5 V
$t_{rr}$	$I_F = 25A, -di/dt = 100 A/\mu s, V_R = 100V$		350	ns
$Q_{rr}$			4	$\mu C$

IXYS reserves the right to change limits, test conditions, and dimensions.

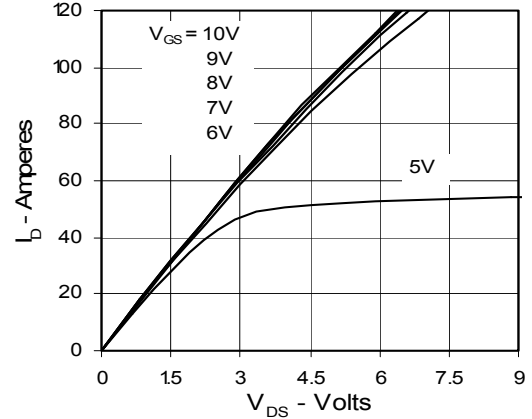
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343

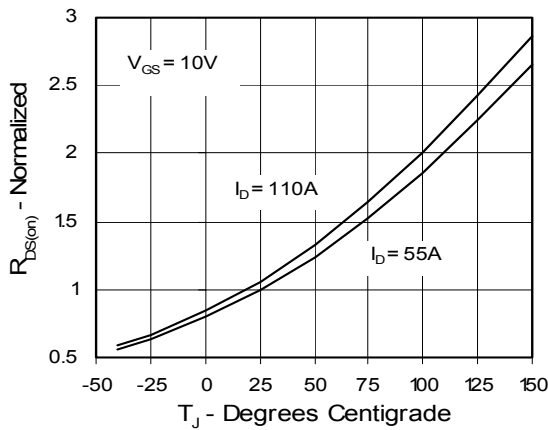
**Fig. 1. Output Characteristics  
@ 25 Deg. C**



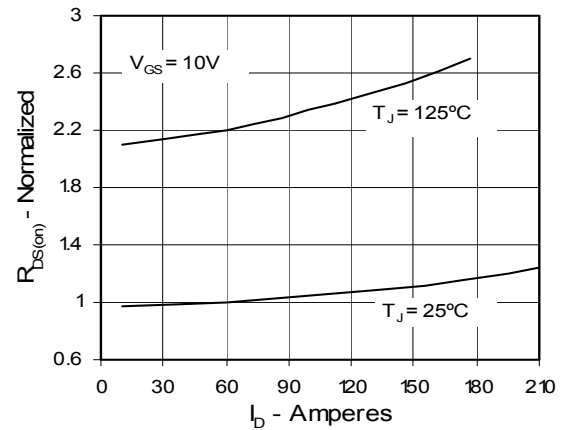
**Fig. 2. Output Characteristics  
@ 125 Deg. C**



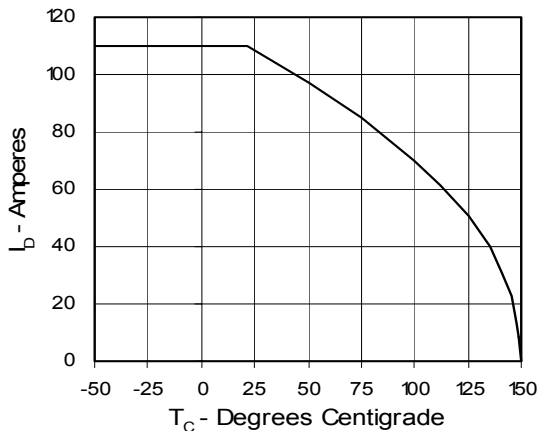
**Fig. 3.  $R_{DS(on)}$  Normalized to  $I_{D25}$  Value vs.  
Junction Temperature**



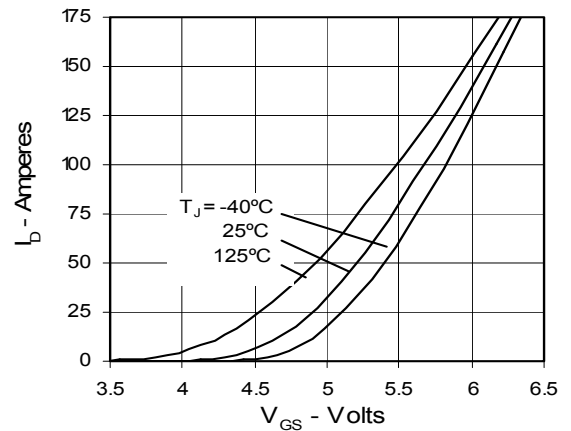
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_{D25}$   
Value vs.  $I_D$**



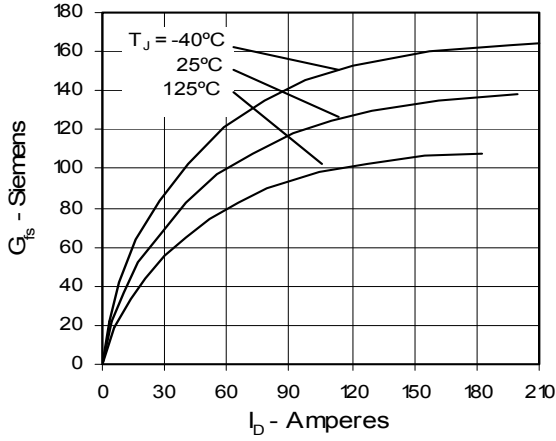
**Fig. 5. Drain Current vs. Case  
Temperature**



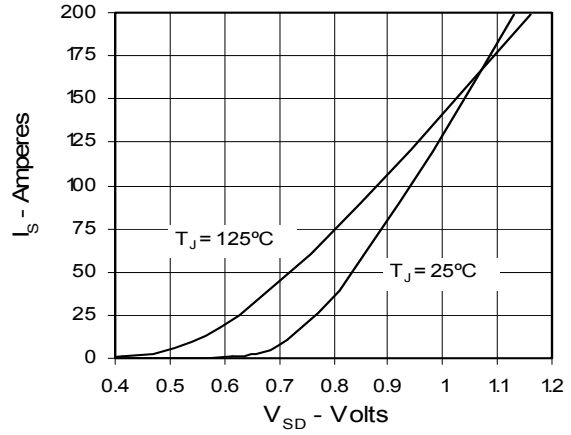
**Fig. 6. Input Admittance**



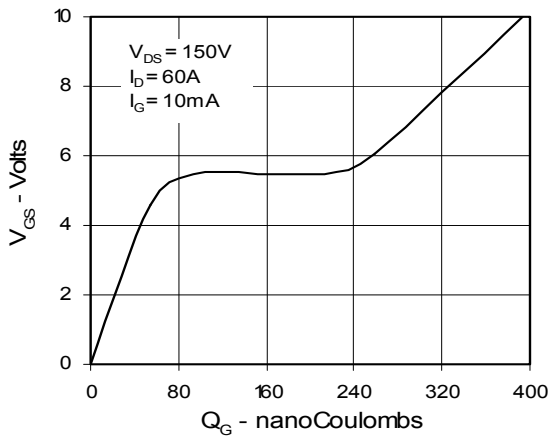
**Fig. 7. Transconductance**



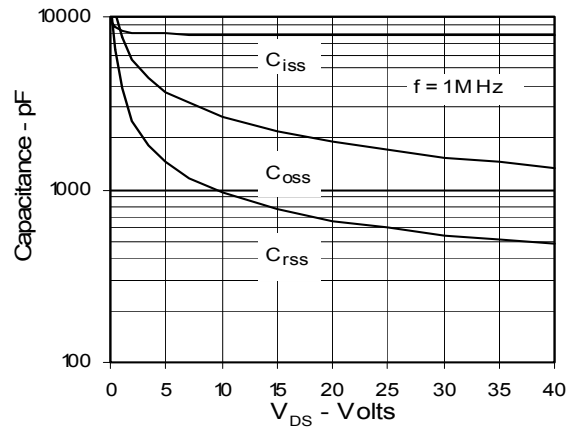
**Fig. 8. Source Current vs. Source-To-Drain Voltage**



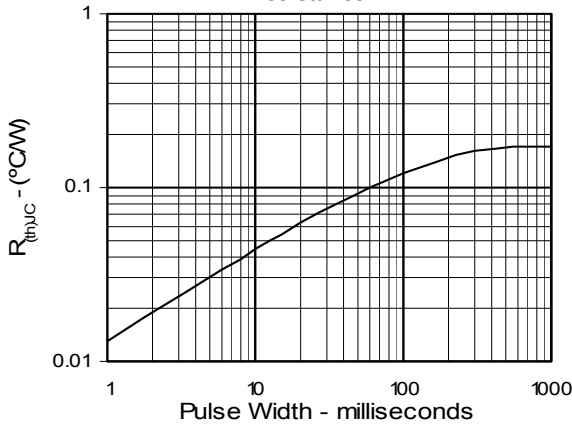
**Fig. 9. Gate Charge**



**Fig. 10. Capacitance**



**Fig. 11. Maximum Transient Thermal Resistance**



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4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343